

74LVC3G14

Triple inverting Schmitt trigger with 5 V tolerant input

Rev. 07 — 12 June 2008

Product data sheet

1. General description

The 74LVC3G14 provides three inverting buffers with Schmitt trigger action.

The inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of this device in a mixed 3.3 V and 5 V environment. Schmitt trigger action at the inputs makes the circuit tolerant of slower input rise and fall time. This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. Features

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant input/output for interfacing with 5 V logic
- High noise immunity
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- ± 24 mA output drive ($V_{CC} = 3.0$ V)
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Unlimited rise and fall times
- Multiple package options
- Specified from -40 °C to $+85$ °C and -40 °C to $+125$ °C.

3. Applications

- Wave and pulse shaper for highly noisy environment
- Astable multivibrator
- Monostable multivibrator.

4. Ordering information

Table 1. Ordering information

Type number	Package				Version
	Temperature range	Name	Description		
74LVC3G14DP	-40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm		SOT505-2
74LVC3G14DC	-40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm		SOT765-1
74LVC3G14GT	-40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 × 1.95 × 0.5 mm		SOT833-1
74LVC3G14GD	-40 °C to +125 °C	XSON8U	plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body 3 × 2 × 0.5 mm		SOT996-2
74LVC3G14GM	-40 °C to +125 °C	XQFN8U	plastic extremely thin quad flat package; no leads; 8 terminals; UTLP based; body 1.6 × 1.6 × 0.5 mm		SOT902-1

5. Marking

Table 2. Marking codes

Type number	Marking code
74LVC3G14DP	V14
74LVC3G14DC	V14
74LVC3G14GT	V14
74LVC3G14GD	V14
74LVC3G14GM	V14

6. Functional diagram

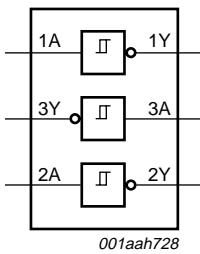


Fig 1. Logic symbol

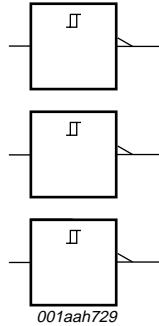
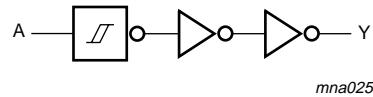


Fig 2. IEC logic symbol



**Fig 3. Logic diagram
(one Schmitt trigger)**

7. Pinning information

7.1 Pinning

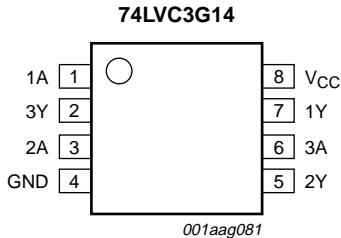


Fig 4. Pin configuration SOT505-2 (TSSOP8) and SOT765-1 (VSSOP8)

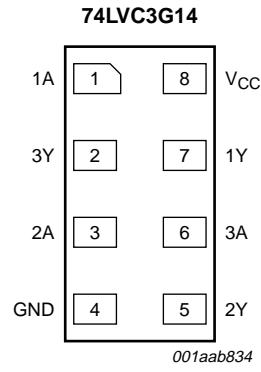


Fig 5. Pin configuration SOT833-1 (XSON8)

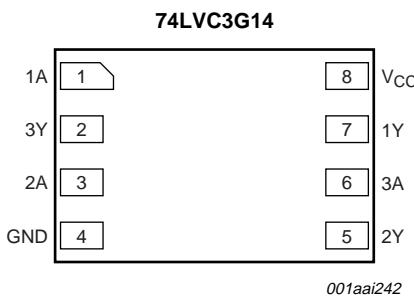


Fig 6. Pin configuration SOT996-2 (XSON8U)

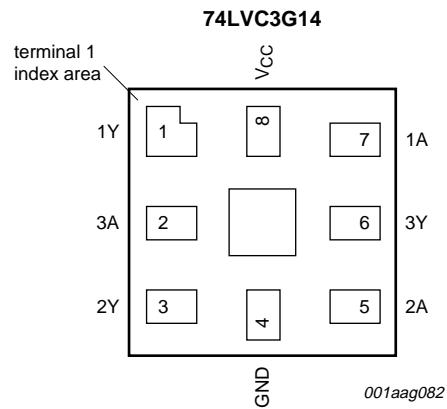


Fig 7. Pin configuration SOT902-1 (XQFN8U)

7.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	SOT505-2, SOT765-1, SOT833-1 and SOT996-2	SOT902-1	
1A, 2A, 3A	1, 3, 6	7, 5, 2	data input
1Y, 2Y, 3Y	7, 5, 2	1, 3, 6	data output
GND	4	4	ground (0 V)
V _{CC}	8	8	supply voltage

8. Functional description

Table 4. Function table [1]

Input nA	Output nY
L	H
H	L

[1] H = HIGH voltage level; L = LOW voltage level

9. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+6.5	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
V _I	input voltage		[1]	-0.5	+6.5
I _{OK}	output clamping current	V _O > V _{CC} or V _O < 0 V	-	±50	mA
V _O	output voltage	Active mode	[1][2]	-0.5	V _{CC} + 0.5
		Power-down mode	[1][2]	-0.5	+6.5
I _O	output current	V _O = 0 V to V _{CC}	-	±50	mA
I _{CC}	supply current		-	100	mA
I _{GND}	ground current		-100	-	mA
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C	[3]	-	250 mW
T _{stg}	storage temperature		-65	+150	°C

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When V_{CC} = 0 V (Power-down mode), the output voltage can be 5.5 V in normal operation.

[3] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.

For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K.

For XSON8, XSON8U and XQFN8U packages: above 45 °C the value of P_{tot} derates linearly with 2.4 mW/K.

10. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		1.65	5.5	V
V _I	input voltage		0	5.5	V
V _O	output voltage	Active mode	0	V _{CC}	V
		Power-down mode; V _{CC} = 0 V	0	5.5	V
T _{amb}	ambient temperature		-40	+125	°C

11. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ [1]	Max	Unit
T_{amb} = -40 °C to +85 °C						
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} I _O = -100 µA; V _{CC} = 1.65 V to 5.5 V I _O = -4 mA; V _{CC} = 1.65 V I _O = -8 mA; V _{CC} = 2.3 V I _O = -12 mA; V _{CC} = 2.7 V I _O = -24 mA; V _{CC} = 3.0 V I _O = -32 mA; V _{CC} = 4.5 V	V _{CC} - 0.1	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} I _O = 100 µA; V _{CC} = 1.65 V to 5.5 V I _O = 4 mA; V _{CC} = 1.65 V I _O = 8 mA; V _{CC} = 2.3 V I _O = 12 mA; V _{CC} = 2.7 V I _O = 24 mA; V _{CC} = 3.0 V I _O = 32 mA; V _{CC} = 4.5 V	-	-	0.1	V
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	±0.1	±5	µA
I _{OFF}	power-off leakage current	V _I or V _O = 5.5 V; V _{CC} = 0 V	-	±0.1	±10	µA
I _{CC}	supply current	V _I = 5.5 V or GND; I _O = 0 A; V _{CC} = 1.65 V to 5.5 V	-	0.1	10	µA
ΔI _{CC}	additional supply current	V _I = V _{CC} - 0.6 V; I _O = 0 A; V _{CC} = 2.3 V to 5.5 V	-	5	500	µA
C _I	input capacitance	V _{CC} = 3.3 V; V _I = GND to V _{CC}	-	3.5	-	pF
T_{amb} = -40 °C to +125 °C						
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} I _O = -100 µA; V _{CC} = 1.65 V to 5.5 V I _O = -4 mA; V _{CC} = 1.65 V I _O = -8 mA; V _{CC} = 2.3 V I _O = -12 mA; V _{CC} = 2.7 V I _O = -24 mA; V _{CC} = 3.0 V I _O = -32 mA; V _{CC} = 4.5 V	V _{CC} - 0.1	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} I _O = 100 µA; V _{CC} = 1.65 V to 5.5 V I _O = 4 mA; V _{CC} = 1.65 V I _O = 8 mA; V _{CC} = 2.3 V I _O = 12 mA; V _{CC} = 2.7 V I _O = 24 mA; V _{CC} = 3.0 V I _O = 32 mA; V _{CC} = 4.5 V	-	-	0.1	V
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	±20	µA

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ [1]	Max	Unit
I _{OFF}	power-off leakage current	V _I or V _O = 5.5 V; V _{CC} = 0 V	-	-	±20	μA
I _{CC}	supply current	V _I = 5.5 V or GND; I _O = 0 A; V _{CC} = 1.65 V to 5.5 V	-	-	40	μA
ΔI _{CC}	additional supply current	V _I = V _{CC} - 0.6 V; I _O = 0 A; V _{CC} = 2.3 V to 5.5 V	-	-	5000	μA

[1] All typical values are measured at maximum V_{CC} and T_{amb} = 25 °C.**Table 8. Transfer characteristics**Voltages are referenced to GND (ground = 0 V; for test circuit see [Figure 9](#)

Symbol	Parameter	Conditions	−40 °C to +85 °C			−40 °C to +125 °C		Unit	
			Min	Typ [1]	Max	Min	Max		
V _{T+}	positive-going threshold voltage	see Figure 10 and Figure 11	V _{CC} = 1.8 V	0.70	1.10	1.50	0.70	1.70	V
			V _{CC} = 2.3 V	1.00	1.40	1.80	1.00	2.00	V
			V _{CC} = 3.0 V	1.30	1.76	2.20	1.30	2.40	V
			V _{CC} = 4.5 V	1.90	2.47	3.10	1.90	3.30	V
			V _{CC} = 5.5 V	2.20	2.91	3.60	2.20	3.80	V
V _{T−}	negative-going threshold voltage	see Figure 10 and Figure 11	V _{CC} = 1.8 V	0.25	0.61	0.90	0.25	1.10	V
			V _{CC} = 2.3 V	0.40	0.80	1.15	0.40	1.35	V
			V _{CC} = 3.0 V	0.60	1.04	1.50	0.60	1.70	V
			V _{CC} = 4.5 V	1.00	1.55	2.00	1.00	2.20	V
			V _{CC} = 5.5 V	1.20	1.86	2.30	1.20	2.50	V
V _H [2]	hysteresis voltage	see Figure 10 , Figure 11 and Figure 12	V _{CC} = 1.8 V	0.15	0.49	1.00	0.15	1.20	V
			V _{CC} = 2.3 V	0.25	0.60	1.10	0.25	1.30	V
			V _{CC} = 3.0 V	0.40	0.73	1.20	0.40	1.40	V
			V _{CC} = 4.5 V	0.60	0.92	1.50	0.60	1.70	V
			V _{CC} = 5.5 V	0.70	1.02	1.70	0.70	1.90	V

[1] All typical values are measured at T_{amb} = 25 °C[2] V_H = V_{T+} − V_{T−}

12. Dynamic characteristics

Table 9. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V). For test circuit see [Figure 9](#).

Symbol	Parameter	Conditions	−40 °C to +85 °C			−40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
t _{pd}	propagation delay nA to nY; see Figure 8	[2]	V _{CC} = 1.65 V to 1.95 V	1.0	4.2	11.0	1.0	12.0 ns
			V _{CC} = 2.3 V to 2.7 V	0.5	3.0	6.5	0.5	7.2 ns
			V _{CC} = 2.7 V	0.5	3.8	7.0	0.5	7.7 ns
			V _{CC} = 3.0 V to 3.6 V	0.5	3.2	6.0	0.5	6.7 ns
			V _{CC} = 4.5 V to 5.5 V	0.5	2.4	4.3	0.5	4.7 ns
C _{PD}	power dissipation capacitance	V _I = GND to V _{CC} ; V _{CC} = 3.3 V [3]	-	-	18.1	-	-	pF

[1] Typical values are measured at T_{amb} = 25 °C and V_{CC} = 1.8 V, 2.5 V, 2.7 V, 3.3 V and 5.0 V respectively.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}.

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum(C_L \times V_{CC}^2 \times f_o)$$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

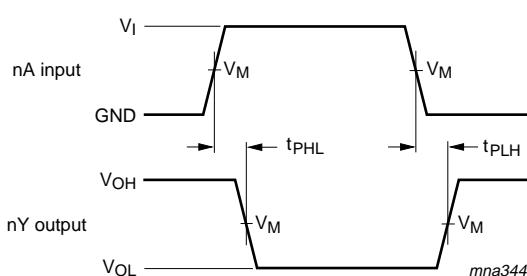
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\sum(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

13. Waveforms

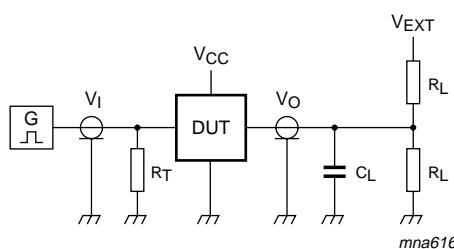


Measurement points are given in [Table 10](#). V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 8. The data input (nA) to output (nY) propagation delays

Table 10. Measurement points

V _{CC}	Input V _M	Output V _M
1.65 V to 1.95 V	0.5 × V _{CC}	0.5 × V _{CC}
2.3 V to 2.7 V	0.5 × V _{CC}	0.5 × V _{CC}
2.7 V	1.5 V	1.5 V
3.0 V to 3.6 V	1.5 V	1.5 V
4.5 V to 5.5 V	0.5 × V _{CC}	0.5 × V _{CC}



Test data is given in [Table 11](#). Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

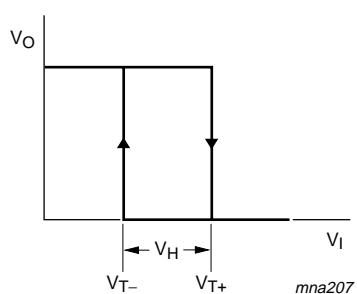
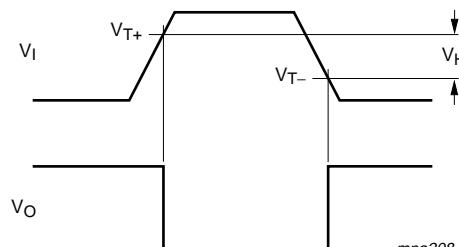
R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

Fig 9. Load circuitry for switching times**Table 11. Test data**

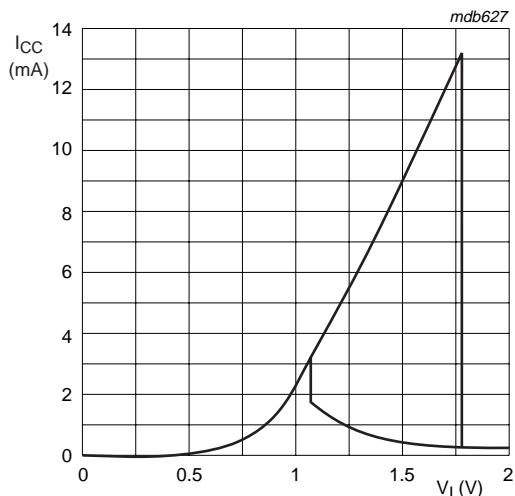
Supply voltage	Input		Load		V _{EXT}
V _{CC}	V _I	t _r = t _f	C _L	R _L	t _{PLH} , t _{PHL}
1.65 V to 1.95 V	V _{CC}	≤ 2.0 ns	30 pF	1 kΩ	open
2.3 V to 2.7 V	V _{CC}	≤ 2.0 ns	30 pF	500 Ω	open
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open
4.5 V to 5.5 V	V _{CC}	≤ 2.5 ns	50 pF	500 Ω	open

14. Waveforms transfer characteristics

**Fig 10. Transfer characteristic**

V_{T+} and V_{T-} limits at 70 % and 20 %.

Fig 11. Definition of V_{T+}, V_{T-} and V_H



$V_{CC} = 3.0$ V

Fig 12. Typical transfer characteristics

15. Application information

The slow input rise and fall times cause additional power dissipation, this can be calculated using the following formula:

$$P_{add} = f_i \times (t_r \times \Delta I_{CC(AV)} + t_f \times \Delta I_{CC(AV)}) \times V_{CC} \text{ where:}$$

P_{add} = additional power dissipation (μW);

f_i = input frequency (MHz);

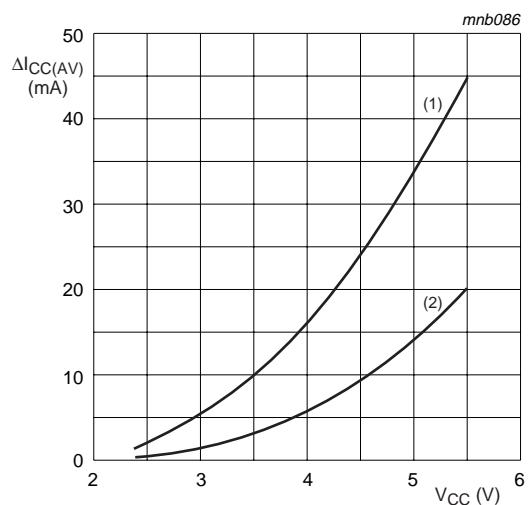
t_r = input rise time (ns); 10 % to 90 %;

t_f = input fall time (ns); 90 % to 10 %;

$\Delta I_{CC(AV)}$ = average additional supply current (μA).

$\Delta I_{CC(AV)}$ differs with positive or negative input transitions, as shown in [Figure 13](#).

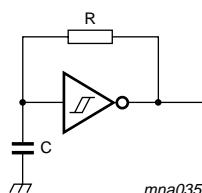
An example of a relaxation circuit using the 74LVC3G14 is shown in [Figure 14](#).



Linear change of V_I between 0.8 V to 2.0 V. All values given are typical unless otherwise specified.

- (1) Positive-going edge.
- (2) Negative-going edge.

Fig 13. $\Delta I_{CC(AV)}$ as a function of V_{CC}



$$f = \frac{I}{T} \approx \frac{I}{0.8 \times RC}$$

Fig 14. Relaxation oscillator

16. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

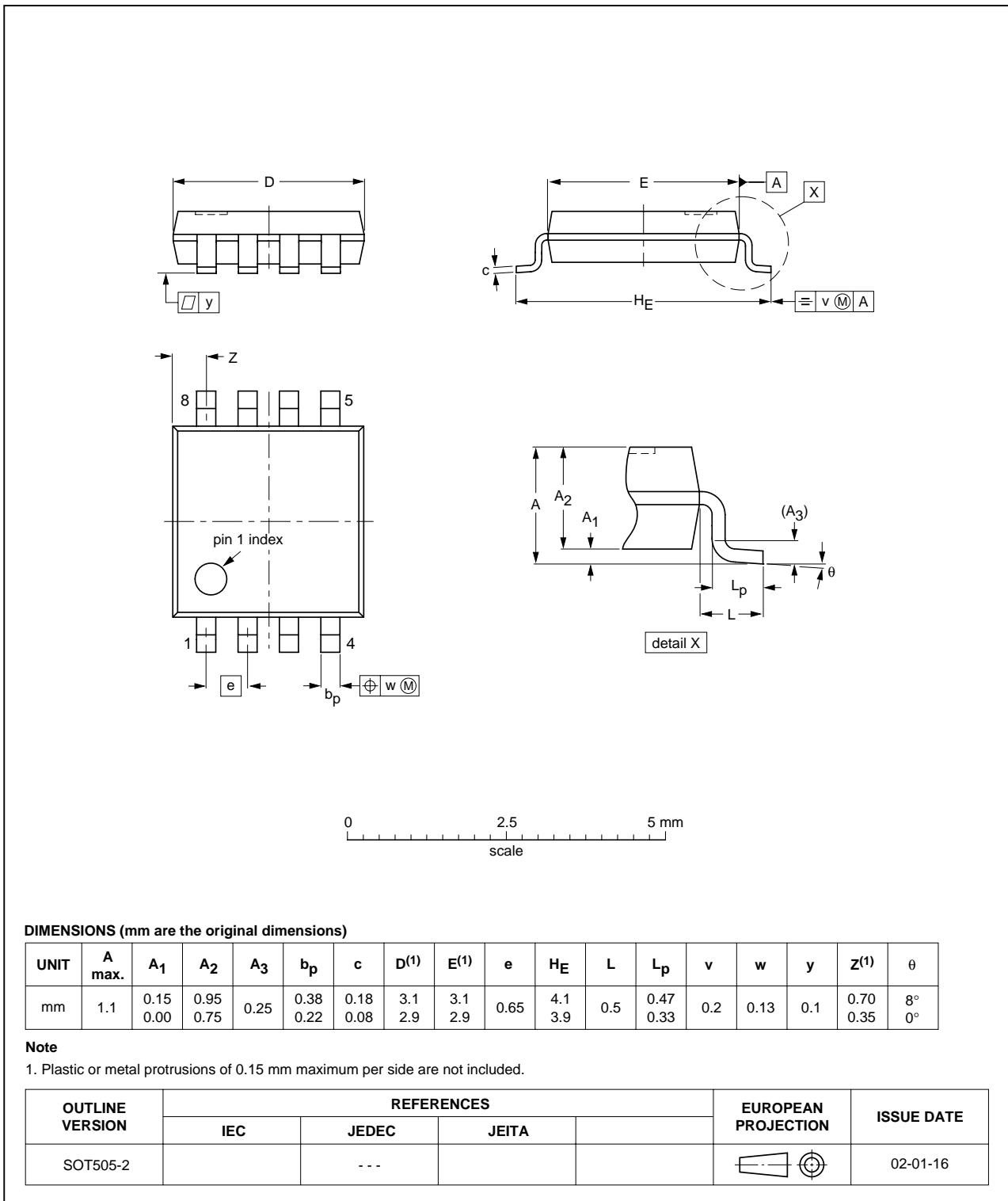


Fig 15. Package outline SOT505-2 (TSSOP8)

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

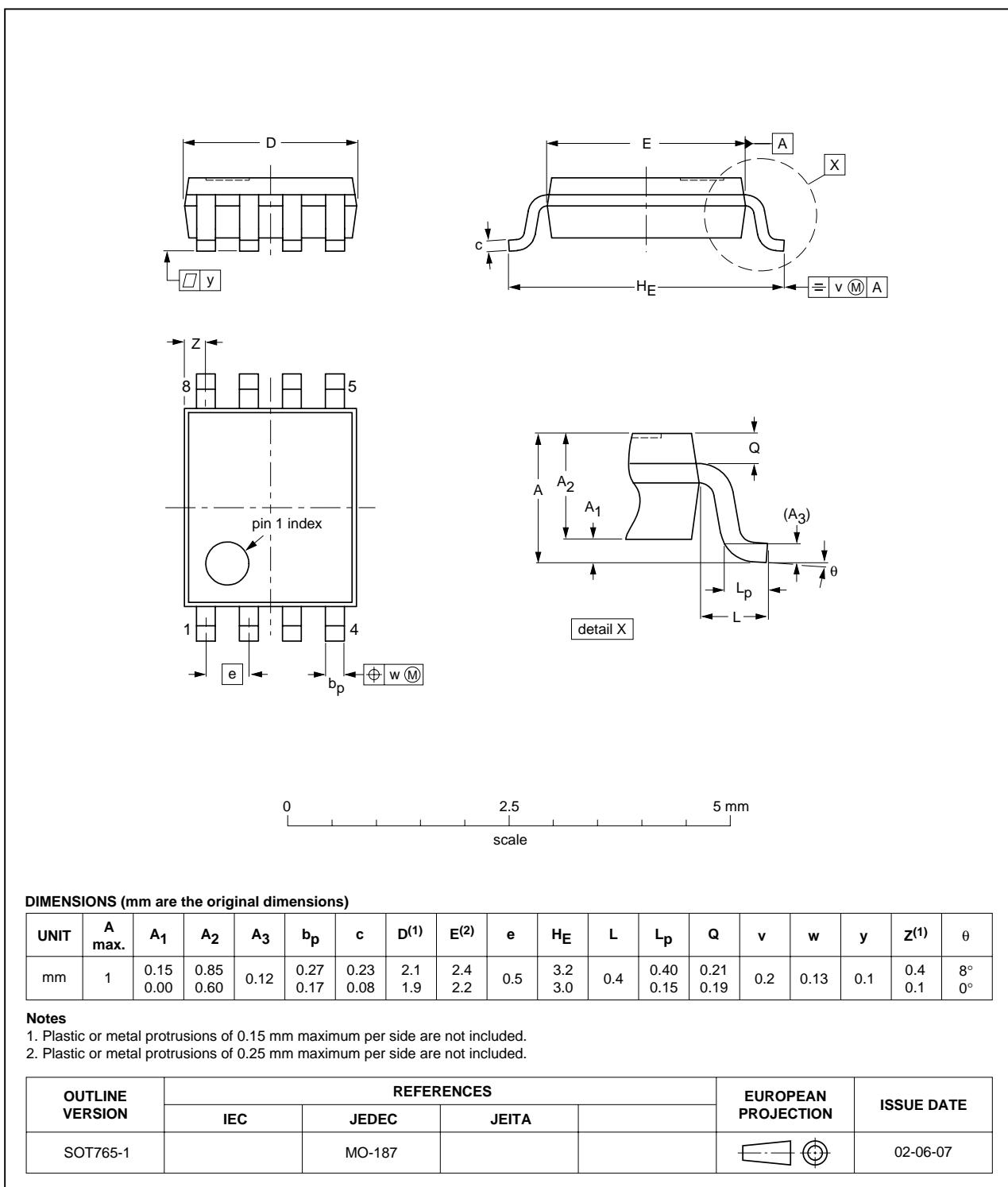


Fig 16. Package outline SOT765-1 (VSSOP8)

XSON8: plastic extremely thin small outline package; no leads; 8 terminals; body 1 x 1.95 x 0.5 mm

SOT833-1

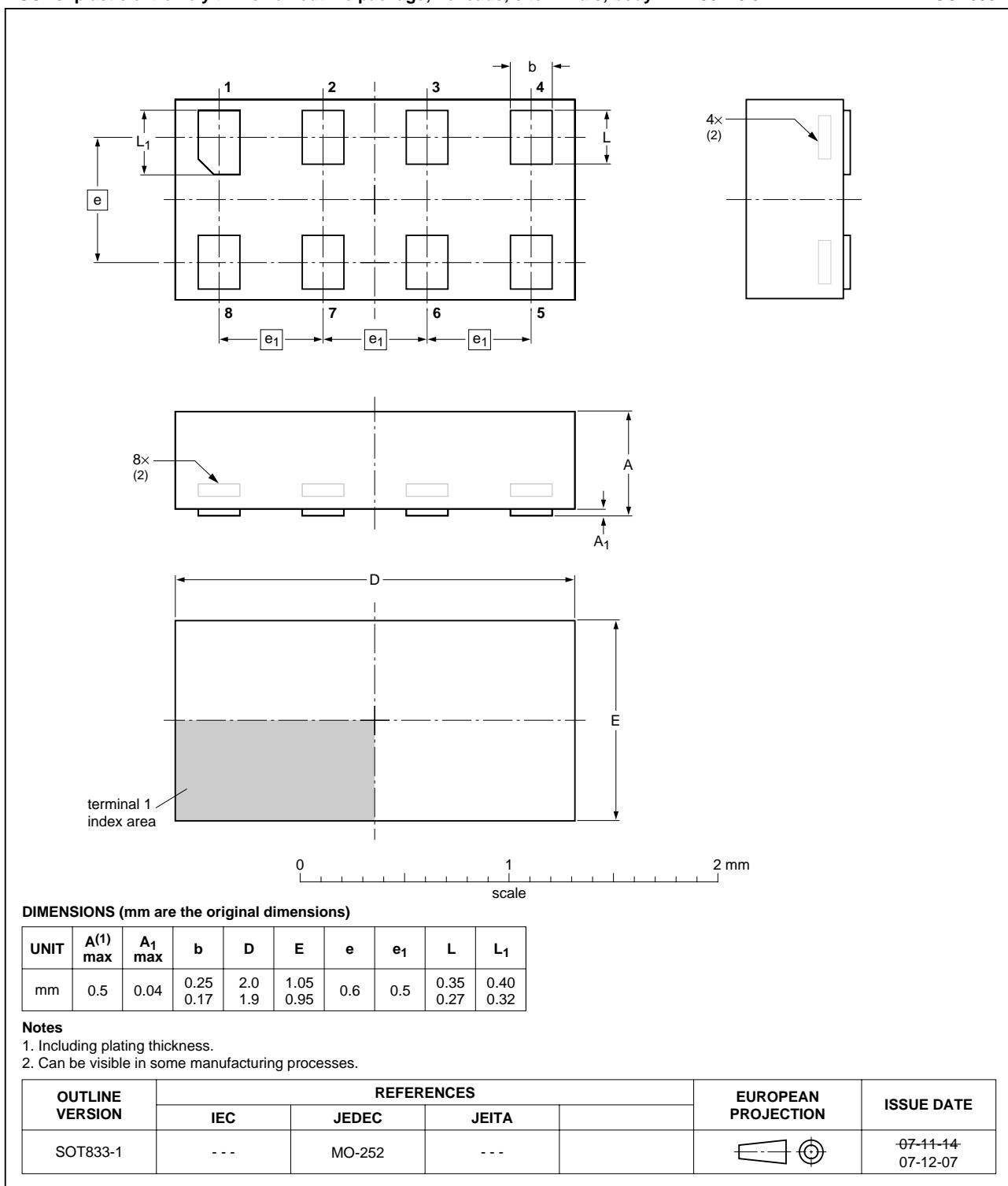


Fig 17. Package outline SOT833-1 (XSON8)

XSON8U: plastic extremely thin small outline package; no leads;
8 terminals; UTLP based; body $3 \times 2 \times 0.5$ mm

SOT996-2

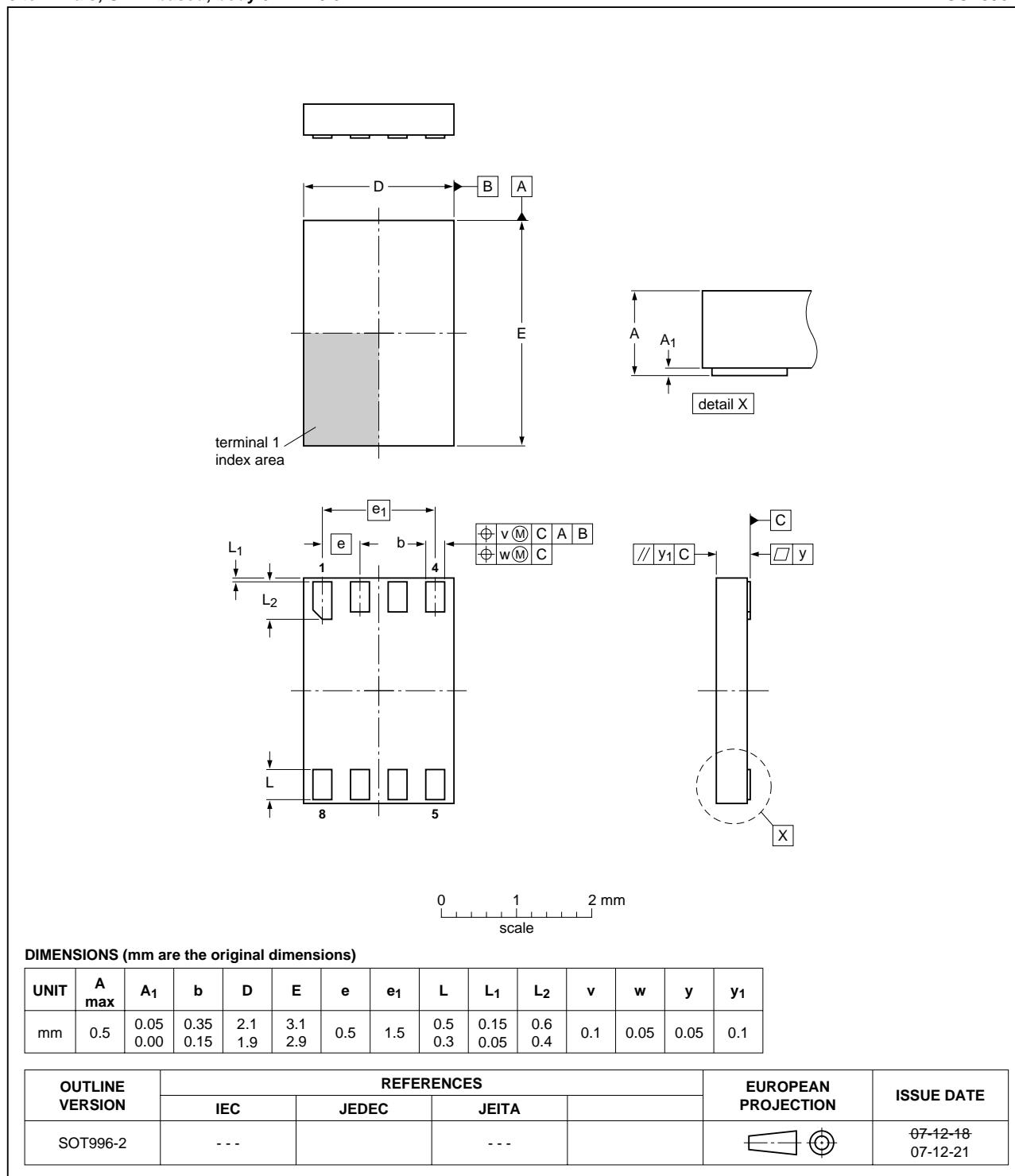


Fig 18. Package outline SOT996-2 (XSON8U)

XQFN8U: plastic extremely thin quad flat package; no leads;
8 terminals; UTLP based; body 1.6 x 1.6 x 0.5 mm

SOT902-1

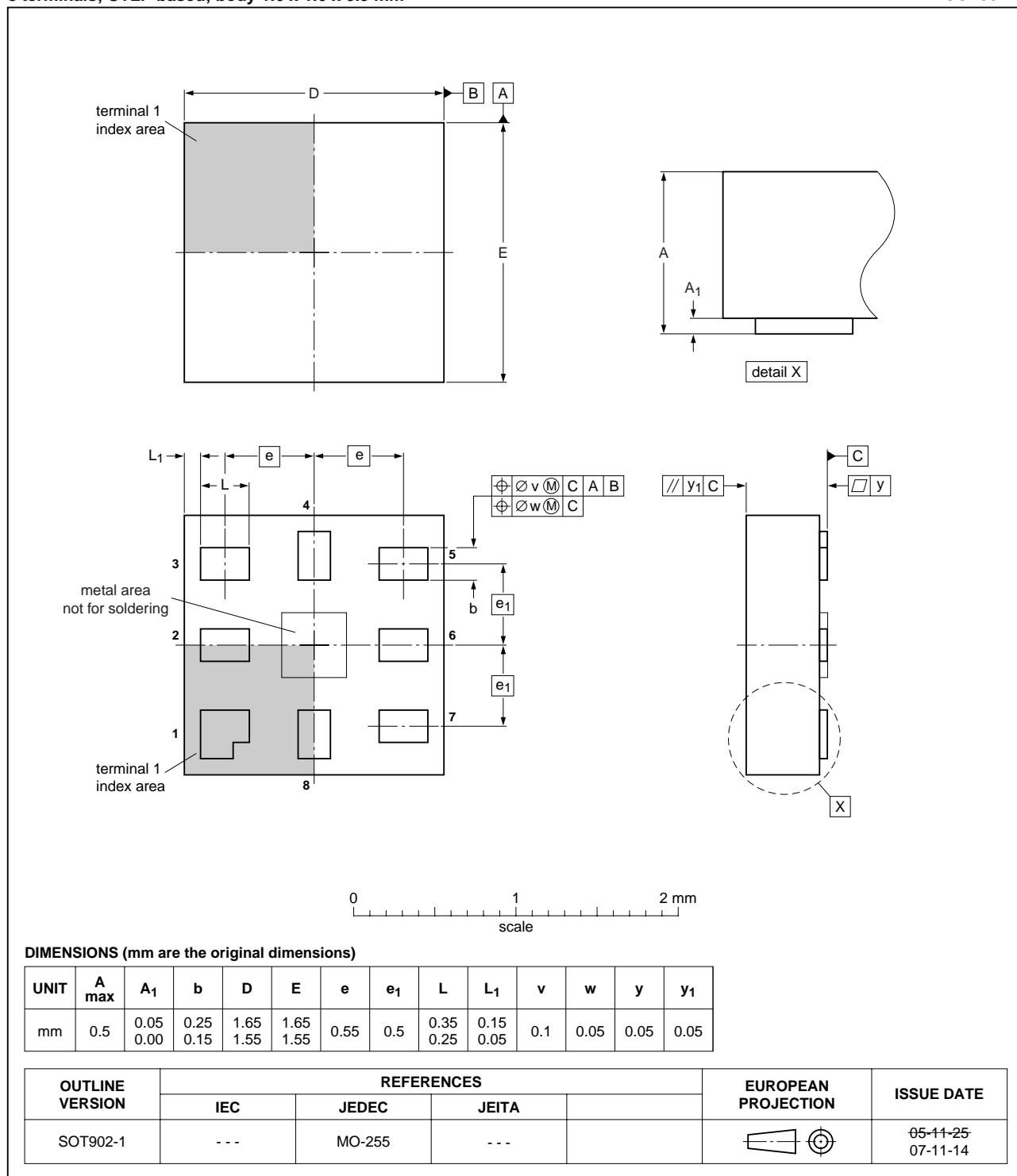


Fig 19. Package outline SOT902-1 (XQFN8U)

17. Abbreviations

Table 12. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic
UTLP	Ultra-Thin Leadless Package

18. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC3G14_7	20080612	Product data sheet	-	74LVC3G14_6
Modifications:				
		• Section 9 : derating factor for TSSOP8 package corrected.		
		• Added type number 74LVC3G14GD (XSON8U package).		
74LVC3G14_6	20080207	Product data sheet	-	74LVC3G14_5
74LVC3G14_5	20071005	Product data sheet	-	74LVC3G14_4
74LVC3G14_4	20070314	Product data sheet	-	74LVC3G14_3
74LVC3G14_3	20050131	Product data sheet	-	74LVC3G14_2
74LVC3G14_2	20041027	Product data sheet	-	74LVC3G14_1
74LVC3G14_1	20040510	Product data sheet	-	-

19. Legal information

19.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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21. Contents

1	General description	1
2	Features	1
3	Applications	1
4	Ordering information	2
5	Marking	2
6	Functional diagram	2
7	Pinning information	3
7.1	Pinning	3
7.2	Pin description	3
8	Functional description	4
9	Limiting values	4
10	Recommended operating conditions	4
11	Static characteristics	5
12	Dynamic characteristics	7
13	Waveforms	7
14	Waveforms transfer characteristics	8
15	Application information	9
16	Package outline	11
17	Abbreviations	16
18	Revision history	16
19	Legal information	17
19.1	Data sheet status	17
19.2	Definitions	17
19.3	Disclaimers	17
19.4	Trademarks	17
20	Contact information	17
21	Contents	18

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